

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The ASI ULBM0.5 is Designed for

**FEATURES:**

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- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	0.4 A
<b>V<sub>CB0</sub></b>	28 V
<b>V<sub>CEO</sub></b>	12 V
<b>V<sub>EBO</sub></b>	4.0 V
<b>P<sub>DISS</sub></b>	2.5 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>θ<sub>JC</sub></b>	70 °C/W

**PACKAGE STYLE .205 4L PILL**

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.976 / 24.800	1.00 / 25.400
B	.976 / 24.800	1.00 / 25.400
C	.028 / 0.700	.031 / 0.800
D	.138 / 3.500	
E	.106 / 2.700	.139 / 3.400
F	.039 / 1.000	.047 / 1.200
G	.004 / 0.100	.006 / 0.150
H	.200 / 5.100	.208 / 5.300

**ORDER CODE: ASI10674**

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 25 mA	12			<b>V</b>
<b>BV<sub>CES</sub></b>	I <sub>C</sub> = 10 mA	28			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 5.0 mA	4.0			<b>V</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V      I <sub>C</sub> = 150 mA	20		---	---
<b>C<sub>ob</sub></b>	V <sub>CB</sub> = 12.5 V      f = 1.0 MHz			4.0	<b>pF</b>
<b>P<sub>G</sub></b>	V <sub>CC</sub> = 12.5 V      P <sub>OUT</sub> = 0.5 W      f = 470 MHz	13			<b>dB</b>